



20V P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

V _{(BR)DSS}	R _{DS(ON)} max	I _D max T _A = +25°C
-20V	1.0Ω @ $V_{GS} = -4.5V$	
	1.2Ω @ V _{GS} = -2.5V	-330mA
	1.6Ω @ V _{GS} = -1.8V	-330IIIA
	3.0Ω @ $V_{GS} = -1.5V$	

Description and Applications

This MOSFET is designed to minimize the on-state resistance $(R_{DS(ON)})$ and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- General Purpose Interfacing Switch
- Power Management Functions
- Analog Switch

Features and Benefits

- Low Package Profile, 0.4mm Maximum Package Height
- 0.48mm² Package Footprint, 16 Times Smaller than SOT23
- Low On-Resistance
- Very Low Gate Threshold Voltage, 1.0V max
- ESD Protected Gate
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

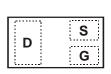
Mechanical Data

- Case: X2-DFN0806-3
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu over Copper Leadframe
- Solderable per MIL-STD-202, Method 208 @4
- Weight: 0.001 grams (Approximate)

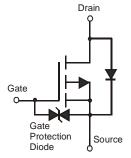








Top View Package Pin Configuration



Equivalent Circuit

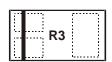
Ordering Information (Note 4)

Part Number	Case	Packaging
DMP21D2UFA-7B	X2-DFN0806-3	10K/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



Top View Bar Denotes Gate and Source Side

R3 = Product Type Marking Code



Maximum Ratings (@ $T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic	Symbol	Value	Units		
Drain-Source Voltage			V_{DSS}	-20	V
Gate-Source Voltage			V _{GSS}	±8	V
Continuous Drain Current (Note 5) V _{GS} = -4.5V	Steady State	$T_A = +25$ °C $T_A = +70$ °C	I _D	-330 -260	mA
Pulsed Drain Current (Note 6)			I _{DM}	1.5	А

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units	
Total Power Dissipation (Note 5)	Steady state	P _D	360	mW
Thermal Resistance, Junction to Ambient (Note 5) Steady state		$R_{\theta JA}$	353	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C	

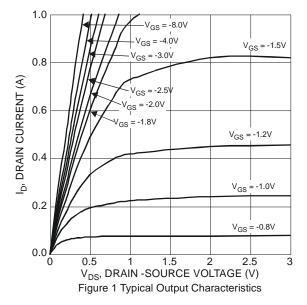
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

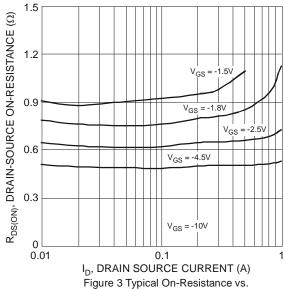
(OTA = 120 O, allious other those opposition)						
Characteristic		Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage		-20	_	_	V	$V_{GS} = 0V, I_D = -250\mu A$
Zero Gate Voltage Drain Current @T _C = +25°C	I _{DSS}	_	_	100	nA	$V_{DS} = -16V, V_{GS} = 0V$
Gate-Source Leakage			_	±10	μΑ	$V_{GS} = \pm 8V$, $V_{DS} = 0V$
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V _{GS(th)}	-0.3	_	-1.0	V	$V_{DS} = V_{GS}$, $I_D = -250\mu A$
		_	0.5	1.0	Ω	$V_{GS} = -4.5V, I_D = -200mA$
Static Drain-Source On-Resistance		_	0.6	1.2		$V_{GS} = -2.5V$, $I_D = -100mA$
Static Dialii-Source Off-Resistance	R _{DS (ON)}	_	0.8	1.6		$V_{GS} = -1.8V, I_D = -50mA$
		_	1.0	3.0		$V_{GS} = -1.5V, I_D = -10mA$
Diode Forward Voltage		_	_	-1.0	V	$V_{GS} = 0V, I_{S} = -10mA$
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C _{iss}	_	49	_	pF	
Output Capacitance	Coss	_	6.5	_	pF	$V_{DS} = -15V, V_{GS} = 0V,$ f = 1.0MHz
Reverse Transfer Capacitance	C _{rss}	_	5.0	_	pF	1 = 1.0WH12
Total Gate Charge	Qg	_	0.8	_	nC	
Gate-Source Charge	Q _{gs}	_	0.1	_	nC	$V_{GS} = -4.5V$, $V_{DS} = -10V$, $I_{D} = -200$ mA
Gate-Drain Charge	Q _{gd}	_	0.2	_	nC	- ID = -200IIIA
Turn-On Delay Time	t _{D(on)}	-	10.3	_	ns	
Turn-On Rise Time		-	37.3	_	ns	$V_{DD} = -15V, V_{GS} = -4.5V,$
Turn-Off Delay Time		-	330	_	ns	$R_G = 2\Omega, I_D = -200 \text{mA}$
Turn-Off Fall Time	t _f	_	163	_	ns]

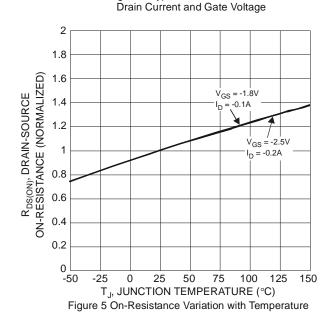
Notes:

- 5. Device mounted on FR-4 PCB, with minimum recommended pad layout.6. Device mounted on minimum recommended pad layout test board, 10µs pulse duty cycle = 1%.
- 7. Short duration pulse test used to minimize self-heating effect.
- 8. Guaranteed by design. Not subject to product testing.

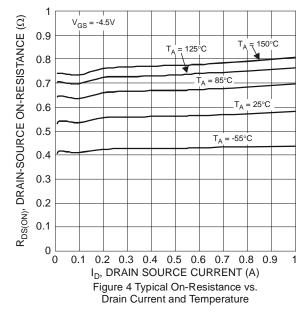








V_{DS} = -5.0V T_A = 85°C = 150°C 0.9 = 25°C 125°C 8.0 -55°C €_{0.7} 0.3 <u>ث</u> 0.2 0.1 0 0 0.5 2 1.5 2.5 V_{GS}, GATE-SOURCE VOLTAGE (V) Figure 2 Typical Transfer Characteristics



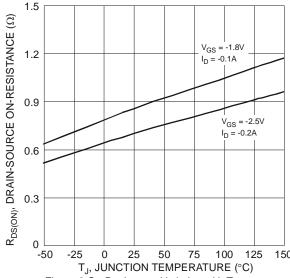


Figure 6 On-Resistance Variation with Temperature



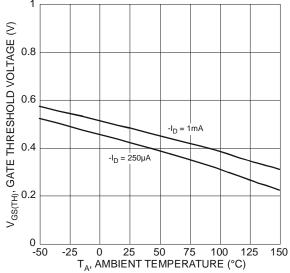
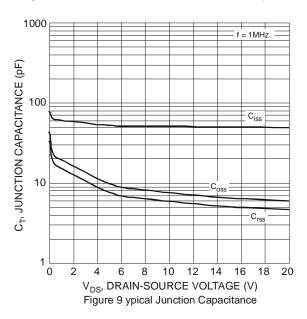
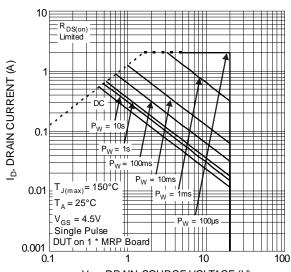
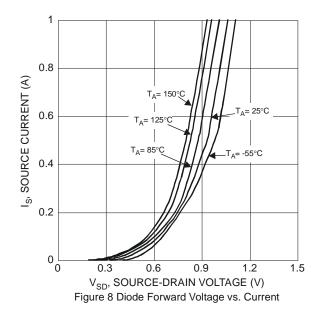


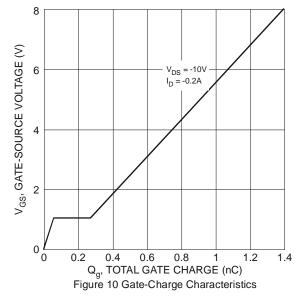
Figure 7 Gate Threshold Variation vs. Ambient Temperature





V_{DS}, DRAIN-SOURCE VOLTAGE (V) Figure 11 SOA, Safe Operation Area

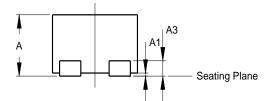


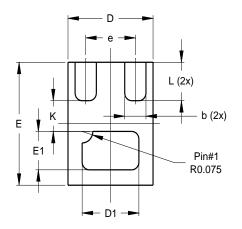




Package Outline Dimensions

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.

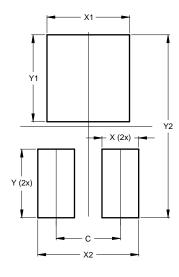




X2-DFN0806-3					
Dim	Min	Max	Тур		
Α	0.375	0.40	0.39		
A1	0	0.05	0.02		
A3	-	-	0.10		
b	0.10	0.20	0.15		
D	0.55	0.65	0.60		
D1	0.35	0.45	0.40		
Е	0.75	0.85	0.80		
E1	0.20	0.30	0.25		
е	-	-	0.35		
K	-	-	0.20		
L	0.20	0.30	0.25		
All Dimensions in mm					

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value		
Dimensions	(in mm)		
С	0.350		
Х	0.200		
X1	0.450		
X2	0.550		
Y	0.375		
Y1	0.475		
Y2	1 000		



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